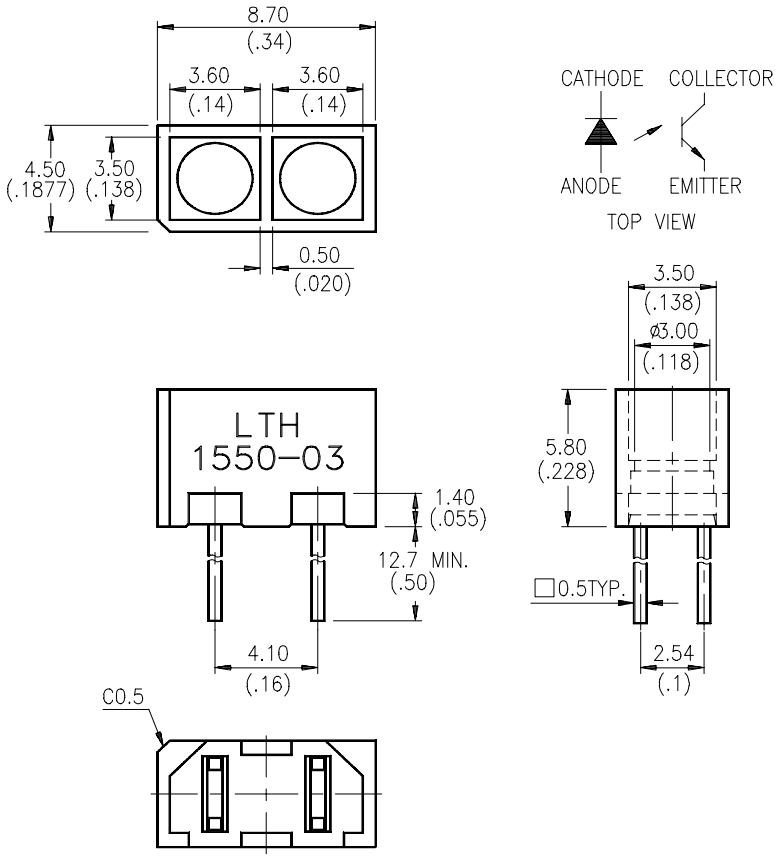
FEATURES

* NON-CONTACT SWITCHING.
* FOR DIRECT PC BOARD OR DUAL-IN-LINE SOCKET MOUNTING.
* FAST SWITCHING SPEED.
* REFLECTIVE OBJECT SENSOR.

PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25mm(.010") unless otherwise noted.
3. Specification are subject to change without notice.

ABSOLUTE MAXIMUM RATINGS AT TA=25℃

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	60	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Current	20	mA
Transistor Power Dissipation	100	mW
IR Diode Peak Forward Current (Pulse Wide = 10 μS, 300 pps)	1	A
Diode Power Dissipation	90	mW
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-35℃ to + 65℃	
Storage Temperature Range	-40℃ to + 100℃	
Lead Soldering Temperature [1.6mm(.063") From Case]	260℃ for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT T_A=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX	UNIT	TEST COND.	BIN NO.
INPUT LED							
Forward Voltage	VF		1.2	1.6	V	I_F = 20mA	
Reverse Current	IR			100	μA	VR=5V	
OUTPUT PHOTOTRANSISTOR							
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	IC=1mA	
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5			V	IE=0.1mA	
Collector-Emitter Dark Current	ICEO			100	nA	VCE=10V	
COUPLER							
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	IC=0.2mA IF=20mA	
On State Collector Current	$I_{C(ON)}$	200		400	μA	VCE=5V IF=20mA d=3.5mm **(90% REFLECT WHITE PAPER)**	BIN A
		300		600			BIN B
		500		1000			BIN C
		800		1600			BIN D

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25℃ Ambient Temperature Unless Otherwise Noted)

Fig.1 NORMALIZED COLLECTOR CURRENT VS. OBJECT DISTANCE

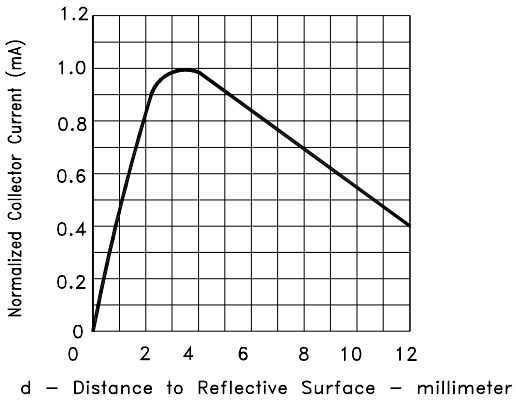


Fig.2 COLLECTOR CURRENT VS.. COLLECTOR VOLTAGE

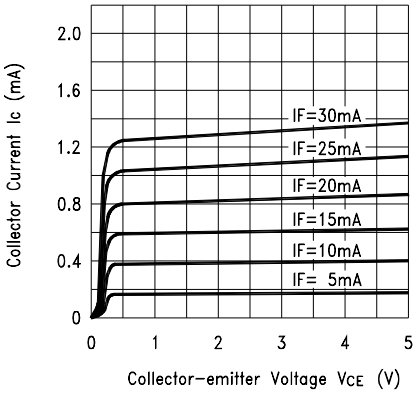


Fig.3 RISE AND FALL TIME VS. LOAD RESISTANCE

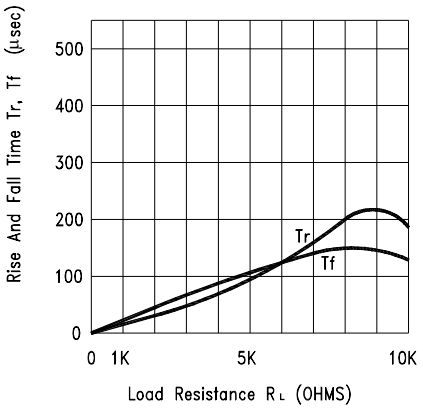


Fig.4 FORWARD CURRENT VS. COLLECTOR-EMITTER SATURATION VOLTAGE